

**REMARKS**

In view of the telephone interview with Examiner Richard A. Booth on May 6, 2002, Applicants respectfully request reconsideration of the finality of the rejection of claims 1-45 of the above-identified patent application.

As Examiner Booth agreed during the telephone interview, Chang does not disclose the limitations of independent claims 1, 6, 16, 21, 31 and 36. Chang does not disclose the steps of forming “a *first oxide layer* over the first conductor layer, a nitride layer over the first oxide layer, and a *second oxide layer* over the nitride layer . . . formed by oxidizing said nitride layer with an ambient containing atomic oxygen,” as independent claim 1 recites (emphasis added). As agreed by Examiner Booth, Chang teaches the formation of a *single* interpoly dielectric layer by depositing an initial oxide layer and then subjecting *the same initial oxide layer* to an ammonia annealing and a wet oxidation. Chang does not teach or suggest the formation of an oxide layer, followed by the formation of a nitride layer and the formation of a second oxide layer, as in the claimed invention.

As further agreed by Examiner Booth during the telephone interview, Chang is also silent about a “method of forming an ONO insulating structure,” much less about an *ONO insulating structure* formed by “depositing a *first oxide layer* over an integrated circuit structure; depositing a nitride layer over said first oxide layer; and growing a *second oxide layer* over said nitride layer. . . by oxidizing said nitride layer in the presence of atomic oxygen,” as independent claim 16 recites (emphasis added). Chang is further silent about a “method of forming a flash memory array,” much less about “a plurality of flash memory cells” formed *inter alia* by forming “a first oxide layer over the first conductor layer, a nitride layer over the first oxide layer, and a second oxide layer over the nitride layer . . . by oxidizing said nitride layer in the presence of atomic oxygen,” as independent claim 31 recites.

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In view of the above, each of the presently pending claims in this application is believed to be in immediate condition for allowance. Accordingly, the Examiner is respectfully requested to withdraw the outstanding rejection of the claims and to pass this application to issue.

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Respectfully submitted,

By 

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